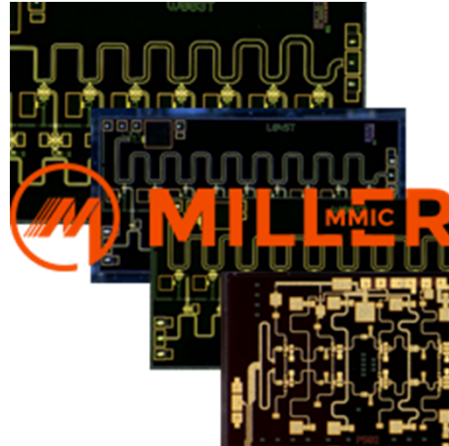


Features

- SPST Absorptive design
- Frequency:DC-20GHz
- Isolation: 55dB
- Insertion Loss: 1.5dB
- Return Loss (ON):20dB
- Control Voltage:0/-5V
- Switching Speed:15ns
- Die Size: 1.54x0.69x 0.1 mm


Typical Applications

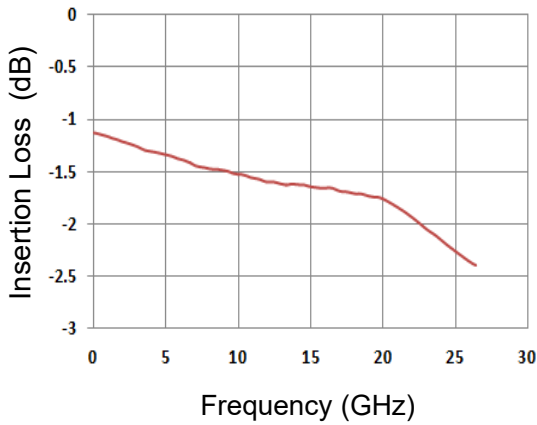
- Voltage control no current
- Fast Switching Speed
- Low Insertion Loss and High Isolation
- Customization available upon request

Electrical Specifications
TA = +25°C, VCTL=0/-5V

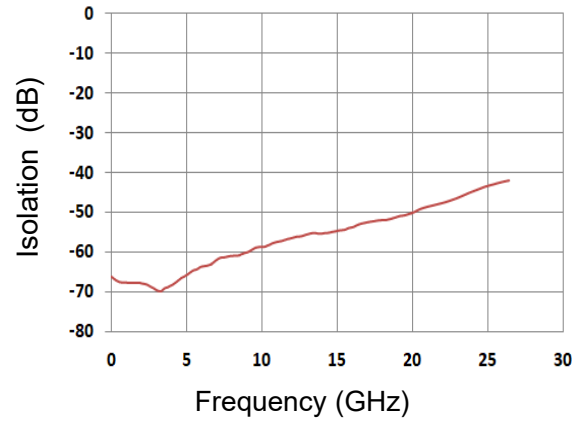
Parameters	Min.	Typ.	Max.	Min.	Typ.	Max.	Units
Frequency	DC - 6		6 - 20				GHz
Insertion Loss		1.25	1.5		1.7	2.0	dB
Isolation	60	65		45	50		dB
Return Loss (ON State)	18	20		18	22		dB
Return Loss (OFF State)	14	15		12	14		dB
Input P-1		18			18		dBm
RF Input power			30			30	dBm
IIP3		28			28		dBm
Switching Speed	15						ns



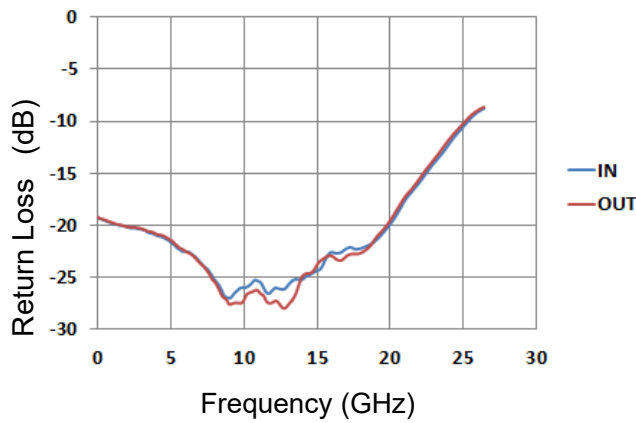
Insertion Loss @25°C



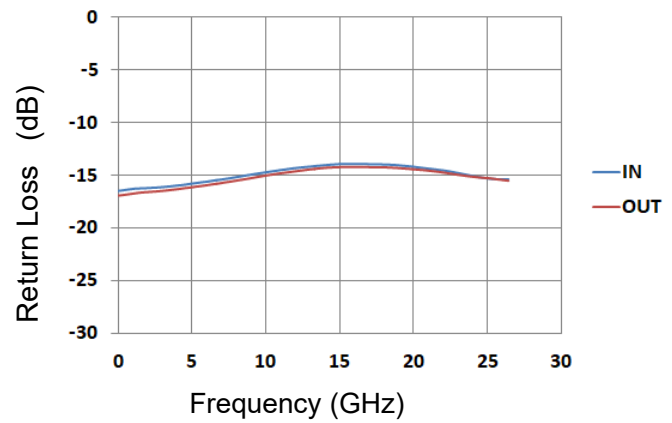
Isolation @25°C



Return Loss (ON) @25°C

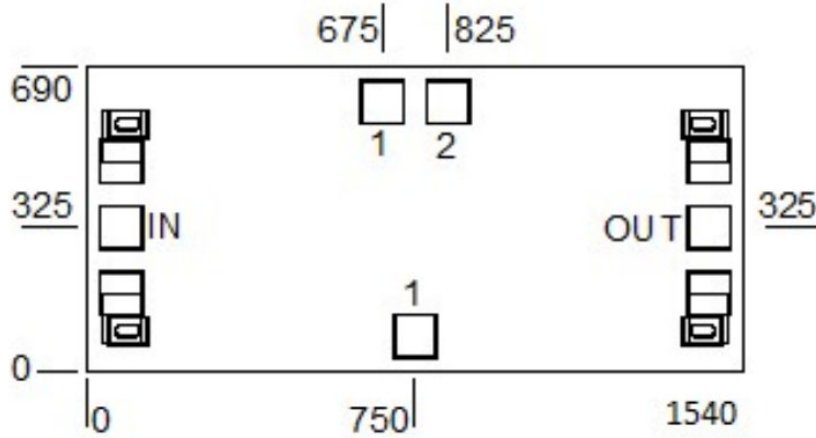


Return Loss (OFF) @25°C





Outline Drawing:
All Dimensions in mm

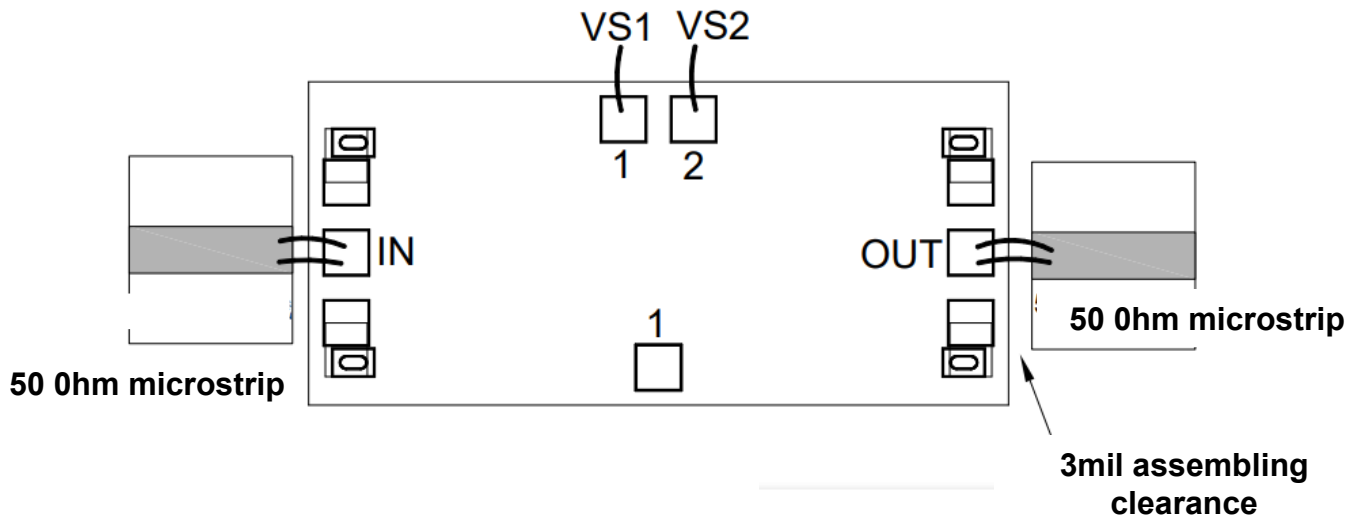


True Table

Control Voltage		State
1	2	IN-OUT
0	-5	OFF
-5	0	ON



Assembly Drawing



Notes:

1. Die thickness: 100um
2. Typical bond pad is 100*100 μm^2
3. Bond pad metalization: Gold
4. Backside metalization: Gold
5. Backside of the die (GND)
6. No connection required for unlabeled bond pads

Maximum Ratings:

1. RF input power: +30dBm
2. Control Voltage: -8~+1V
3. Storage temperature: -65°C to +150°C
3. Operating temperature: -55°C to 125°C